active upper side for at least one integrated circuit for each

of the electronics components and a passive rear side;

implanting impurities from the passive rear side of the semiconductor wafer for forming a buried layer being electrically conductive and having a surface area corresponding in size to a surface area of the passive rear side of the semiconductor substrate;

introducing an electrically conductive annular layer for each of the electronic components from the active upper side of the semiconductor wafer as far as the buried layer in an edge region of the integrated circuit;

producing the integrated circuit within the electrically conductive annular layer for each of the electronic components in the semiconductor substrate defining a semiconductor chip for each of the electronic components; and

packaging the semiconductor chip to form the electronic components with the shielding.

Claim 21 (amended). A method for producing electronic components with shielding, which comprises the following steps:

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providing a semiconductor wafer functioning as a semiconductor substrate having an active upper side for at least one integrated component for each of the electronic components and a passive rear side;

growing an electrically conductive layer formed of an electrically conductive semiconductor material and thereafter an electrically intrinsically conductive layer formed of an electrically intrinsic conductive semiconductor material on the active upper side of the semiconductor wafer by epitaxial growth, the electrically conductive layer becoming a buried layer adjacent the electrically intrinsically conductive layer;

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introducing an electrically conductive annular layer for each of the electronic components from the active upper side of the semiconductor wafer, the electrically conductive annular layer extending through the electrically intrinsically conductive layer as far as the buried layer, the electrically conductive annular layer disposed in an edge region of the semiconductor substrate;

producing the integrated circuit within the electrically conductive annular layer for each of the electronic components in the semiconductor substrate defining a semiconductor chip; and

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packaging the individual conductor chips to form the electronic components with the shielding.